

L Number	Hits	Search Text	DB	Time stamp
1	0	@ad<=20011206 and 'O' adj1 'SiON' adj1 'N' adj1 'SiON' adj1 'O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 13:56
2	0	@ad<=20011206 and 'O/SiON/N/SiON/O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 13:56
3	1	@ad<=20011206 and 'O-SiON-N-SiON-O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 13:56
-	696	(438/400).cccls. and @ad<=20011206	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 11:22
-	6	((438/400).cccls. and @ad<=20011206) and ONO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 11:26
-	0	@ad<=20011206 and 'ONO structure' with 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:34
-	290	@ad<=20011206 and 'ONO structure'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:33
-	160	@ad<=20011206 and 'Oxide' with 'SiON' with 'SiN' with 'SiON' with 'Oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:31
-	3	@ad<=20011206 and 'ONO structure' and 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:40
-	1	@ad<=20011206 and 'multi dielectric layer' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:43
-	26	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:47
-	0	@ad<=20011206 and 'O-SiON-N-SiON-O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:49
-	1393	@ad<=20011206 and oxide and SiON and Nitride and SiON and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:55
-	0	@ad<=20011206 and oxide adj SiON adj Nitride adj SiON adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 12:56

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-	300	@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:28
-	107	((@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 14:52
-	540	@ad<=20011206 and (438/778).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/17 14:32
-	2862	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 08:49
-	2356	((257/324) or (257/314-315) or (257/406) or (257/410)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:50
-	7	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'silane' with 'nitrogen oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 08:59
-	6328	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'SiON' or 'silicon oxynitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:03
-	0	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and SiH4 with N2O with NH3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:04
-	8	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'SiON' with 'deposition'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:09
-	448	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'ammonia'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:11
-	190	((438/778) or (438/787) or (438/790-791) or (438/794) or (438/400) or (438/769-770) or (438/770) or (438/775)).CCLS.) and @ad<=20011206 and 'ammonia' and 'silane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:11
-	194	@ad<=20011206 and 'ammonia' and 'silane' and 'nitrogen oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:16
-	359	@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:27
-	27	@ad<=20011206 and 'ammonia' same 'silane' same 'nitrogen oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/28 09:19

-	0	@ad<=20011206 and 'oxide' same 'silane' same dichloro adj silane with 'nitrogen oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:29
-	0	@ad<=20011206 and 'silane' same 'dichloro silane' with 'nitrogen oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:30
-	3	@ad<=20011206 and 'silane' same 'dichlorosilane' with 'N.sub.2O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:36
-	0	@ad<=20011206 and 'silicon oxide' same 'silane' same 'DCS' same 'N.sub.2O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:37
-	32	@ad<=20011206 and 'silicon oxide' same 'silane' same 'N.sub.2O'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:39
-	25	@ad<=20011206 and 'silicon oxide' same 'silane' same 'nitrous oxide' and 'dichlorosilane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 10:17
-	71	@ad<=20011206 and 'oxide' same 'silane' same 'nitrous oxide' same 'dichlorosilane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 10:51
-	12	@ad<=20011206 and 'oxide' same 'SiH.sub.4' same 'N.sub.2O' same 'SiH.sub.2Cl.sub.2'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 10:29
-	4	@ad<=20011206 and 'silicon oxide' same 'SiH.sub.4' same 'N.sub.2O' same 'SiH.sub.2Cl.sub.2'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 10:37
-	5	((("6127255") or ("5811316") or ("5331191") or ("5202275")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 10:37
-	27	@ad<=20011206 and 'dioxide' same 'silane' same 'nitrous oxide' same 'dichlorosilane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 09:06
-	160	(@ad<=20011206 and 'oxide' with 'SiON' with 'nitride' with 'SiON' with 'oxide') and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 15:20
-	1	"5506178".PN.	USPAT	2003/06/19 15:06
-	45	hisatomi-kiyoshi.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:26
-	20	toshiba.as. and 'ONO' and 'oxynitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 15:28

-	341	toshiba.as. and 'oxynitride'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/19 15:29
-	16	@ad<=20011206 and 'silicon oxynitride' same 'silane' same 'dichlorosilane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 09:09
-	2	@ad<=20011206 and 'SiON' same 'silane' same 'dichlorosilane'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/20 09:07
-	45	hisatomi-kiyoshi.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:26
-	0	@ad<=20011206 and 'oxide' adj2 'SiON' adj2 'nitride' adj2 'SiON' adj2 'oxide'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:50
-	12	@ad<=20011206 and 'ONO' same 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:37
-	296	@ad<=20011206 and 'ONO' and 'buffer layer'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:37
-	271	@ad<=20011206 and 'multi' adj2 'dielectric' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:46
-	19	@ad<=20011206 and 'multi' adj1 'dielectric' same 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:46
-	34	@ad<=20011206 and 'multi' adj 'dielectric' and 'memory'	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:48
-	496	@ad<=20011206 and (257/324).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:51
-	134	@ad<=20011206 and (438/216).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 13:55
-	147	@ad<=20011206 and (438/621).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/24 11:52